HD Communications Corp.

HD32820
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB linear GaAsFET design
Instantaneous wide bandwidth
Designed for EMI/RFI, lab, and general communication applications
Suitable for all single channel modulation standards
Rack mounted system
Local LCD & remote flexible interfaces
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	18.0 - 26.5 GHz	
Power Output CW	80 Watt Min	
Power Gain	49 dB Min	
Power Gain Flatness	4.0 dB p-p Typ	Constant input power
Input Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-30 dBc Typ	38dBm/Tone, Δ = 1MHz
Harmonics	-20 dBc Max	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	1600 Watt Max	
Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	Auto shutdown >5:1 load VSWR
Sample Port Coupling	-40 dB	KF-2.92mm

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing
Shock & Vibration	MIL-STD-810E	Designed to meet

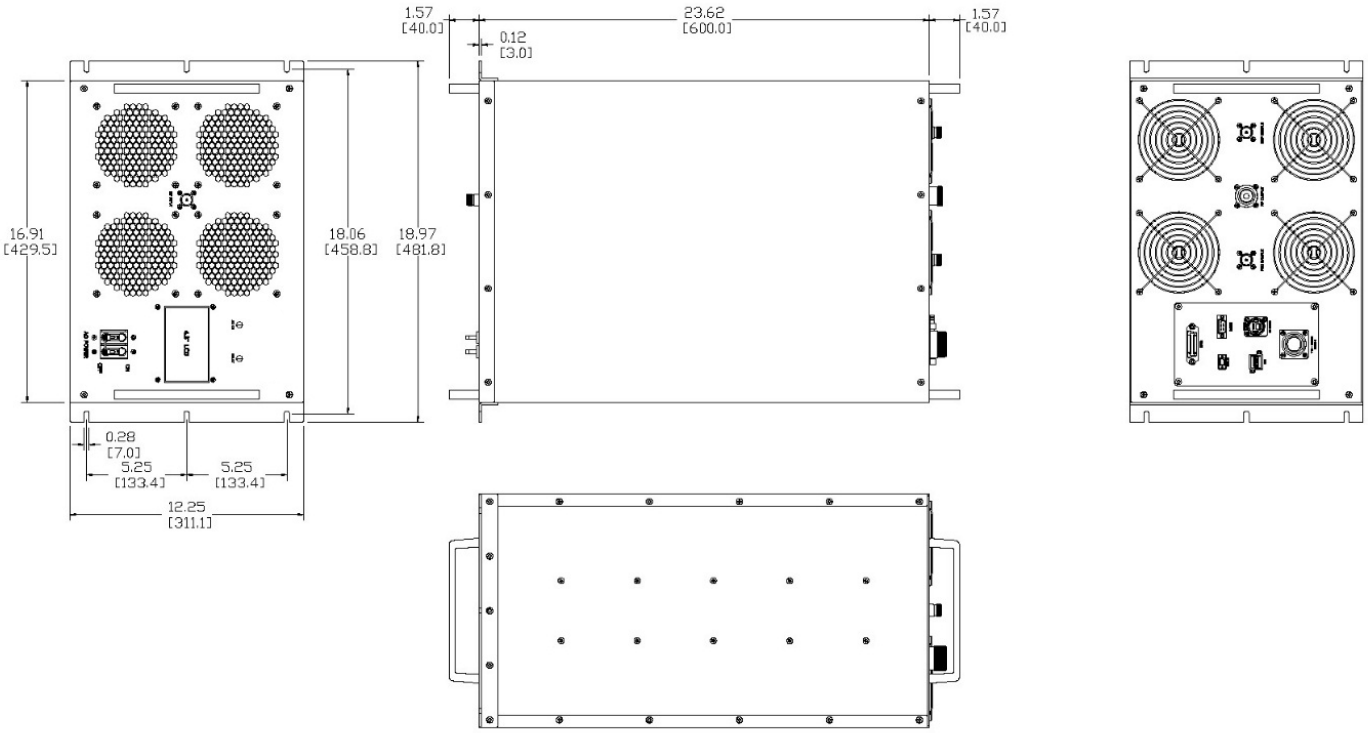
MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	430 x 311 x 600 mm	2x7U - Excluding handles
Weight	40 Kg. Nom	
RF Connectors In / Out / Sample Port	2.9 mm (KF / WR42) K-Female	Rear or Front panel
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	Or equivalent
Cooling	Air-Cooled hybrid design	Built in pump
EMI SERIES: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485, USB Optional GPIB Interface	

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OUTLINE DRAWING (base unit) -x2 rack integrated



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